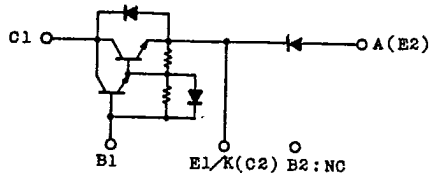


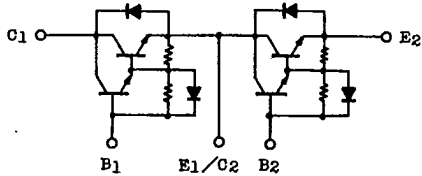


## SEMICONDUCTOR TECHNICAL DATA

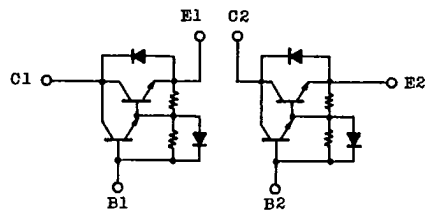
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MG100G2CL1  
MG100G2DL1



MG100G1JL1

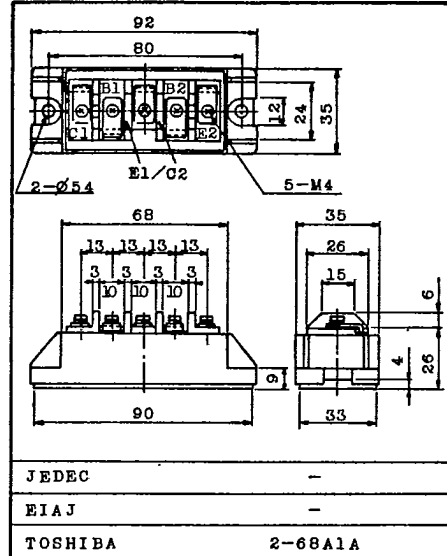


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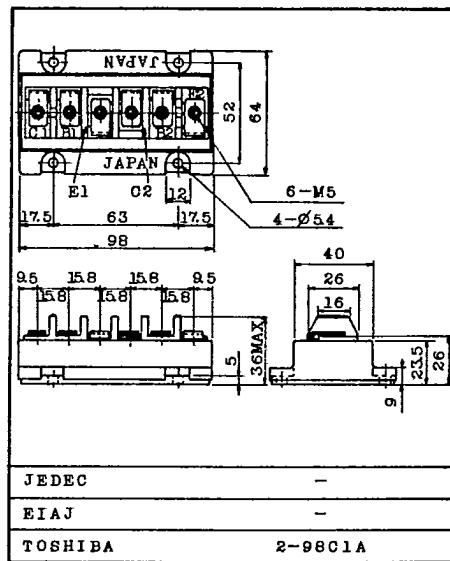
MG100G2DL1

Unit in mm



Weight : 205g

Unit in mm



Weight : 430g

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**SEMICONDUCTOR**  
TECHNICAL DATA

M G 1 0 0 G 1 J L 1  
M G 1 0 0 G 2 C L 1  
M G 1 0 0 G 2 D L 1

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CB0</sub>	600	V
Collector-Emitter Voltage	V <sub>CE0</sub>	600	V
Collector-Emitter Sustaining Voltage	V <sub>CEO(SUS)</sub>	450	V
Emitter-Base Voltage	V <sub>EB0</sub>	6	V
Collector Current	DC I <sub>C</sub>	100	A
	lms I <sub>C</sub>	200	
	DC -I <sub>C</sub>	100	
Base Current	I <sub>B</sub>	5	A
Collector Power Dissipation (Tc=25°C)	P <sub>C</sub>	400	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-40 ~ 125	°C
Isolation Voltage	V <sub>isol</sub>	2500(AC 1 Minute)	V
Screw Torque (Terminal/Mounting)	-	20/30	kg.cm

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I <sub>CB0</sub>	V <sub>CB</sub> =600V, I <sub>E</sub> =0	-	-	2.0	mA	
Emitter Cut-off Current	I <sub>EB0</sub>	V <sub>EB</sub> =6V, I <sub>C</sub> =0	-	-	200	mA	
Collector-Emitter Sustaining Voltage	V <sub>CEO(SUS)</sub>	I <sub>C</sub> =0.5A L=40mH	450	-	-	V	
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =100A	100	-	-	-	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =100A, I <sub>B</sub> =2A	-	-	2.0	V	
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>		-	-	2.7	V	
Emitter-Collector Voltage	V <sub>ECO</sub>	I <sub>E</sub> =100A, I <sub>B</sub> =0	-	-	1.6	V	
Reverse Recovery Time	t <sub>rr</sub>	-I <sub>C</sub> =100A, V <sub>EB</sub> =3V V <sub>CC</sub> =300V, di/dt=100A/μs	-	-	2.0	μs	
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =50V, I <sub>E</sub> =0 f=1MHz	-	1000	-	pF	
Switching Time	Turn-on Time		-	-	2.0	μs	
	Storage Time		t <sub>stg</sub>	-	-		12
	Fall Time		t <sub>f</sub>	-	-		2.0
Thermal Resistance (Junction to Case)	R <sub>th(j-c)</sub>	Transistor	-	-	0.31	°C/W	
		Diode	-	-	1.3		

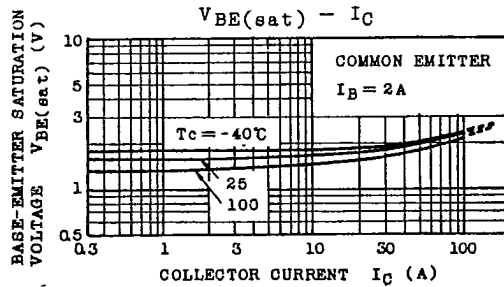
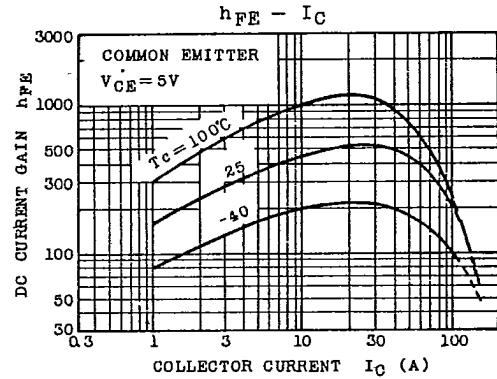
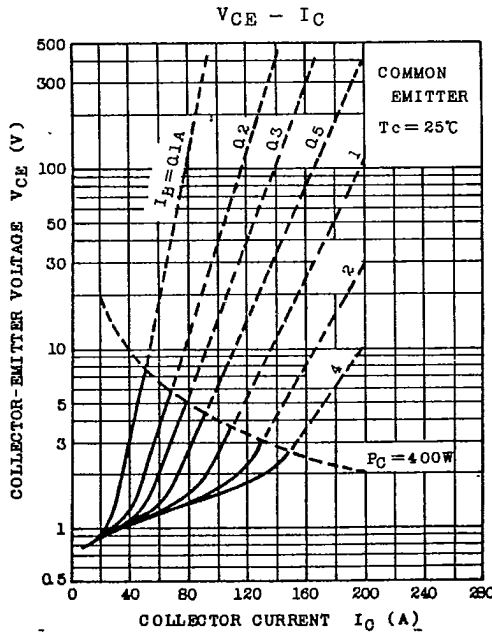
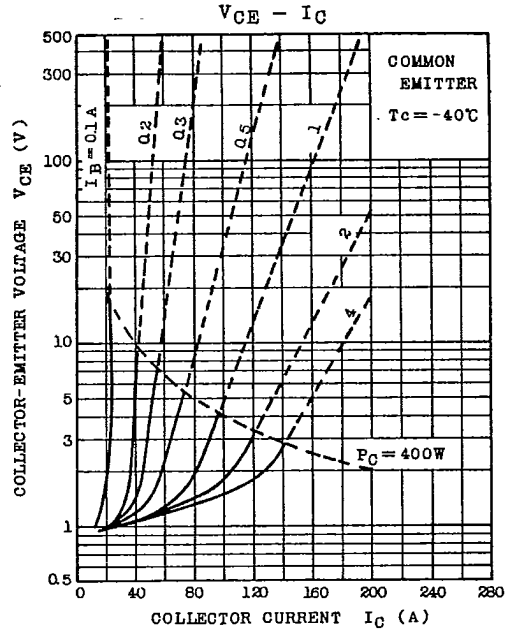
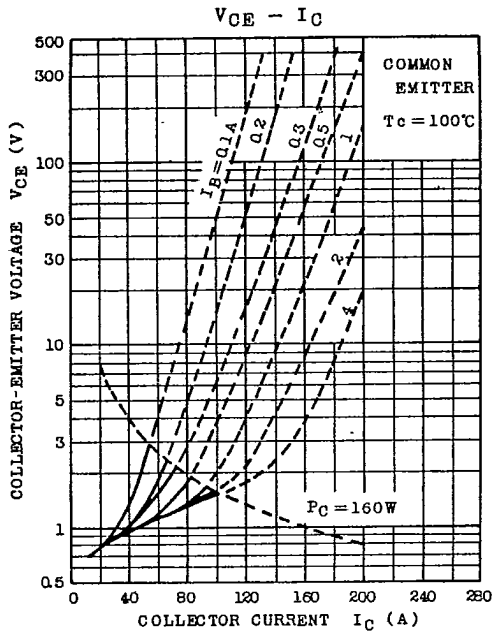
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TECHNICAL DATA

MG100G1JL1  
MG100G2CL1  
MG100G2DL1



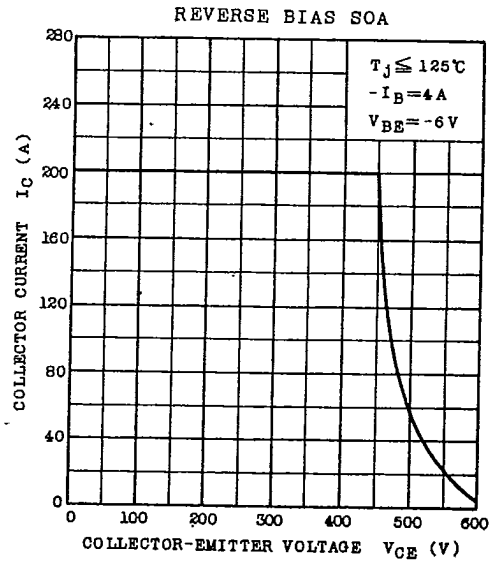
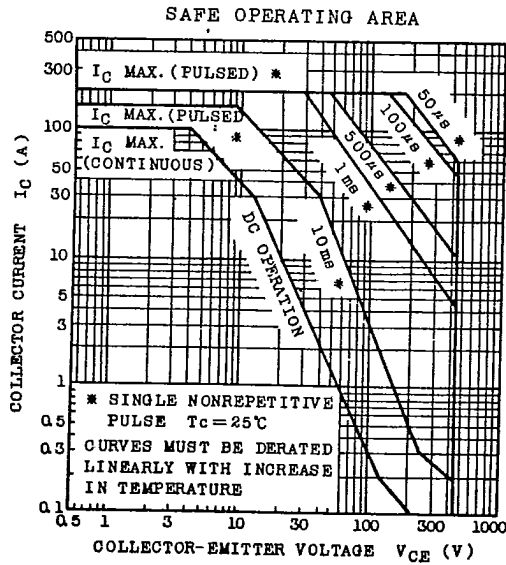
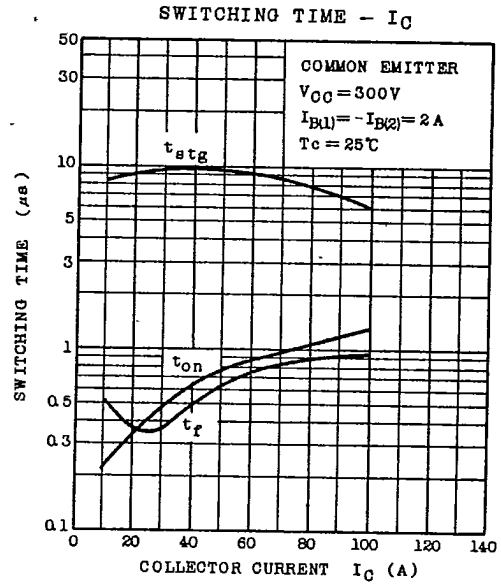
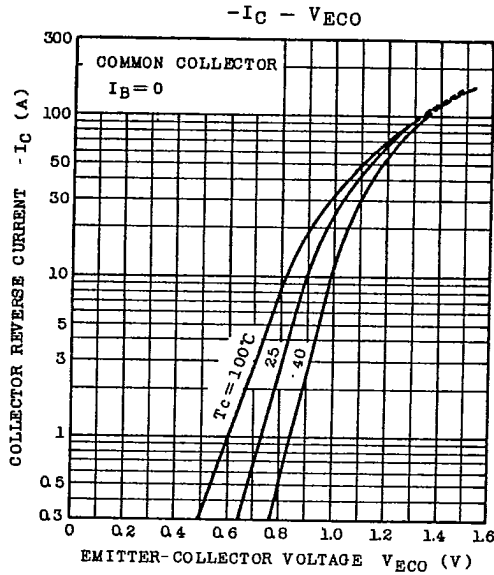
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SEMICONDUCTOR  
TECHNICAL DATA

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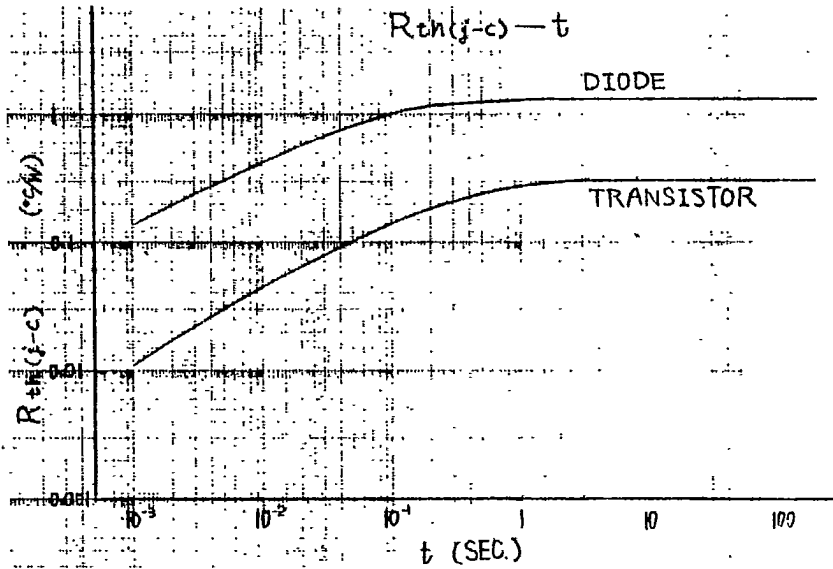
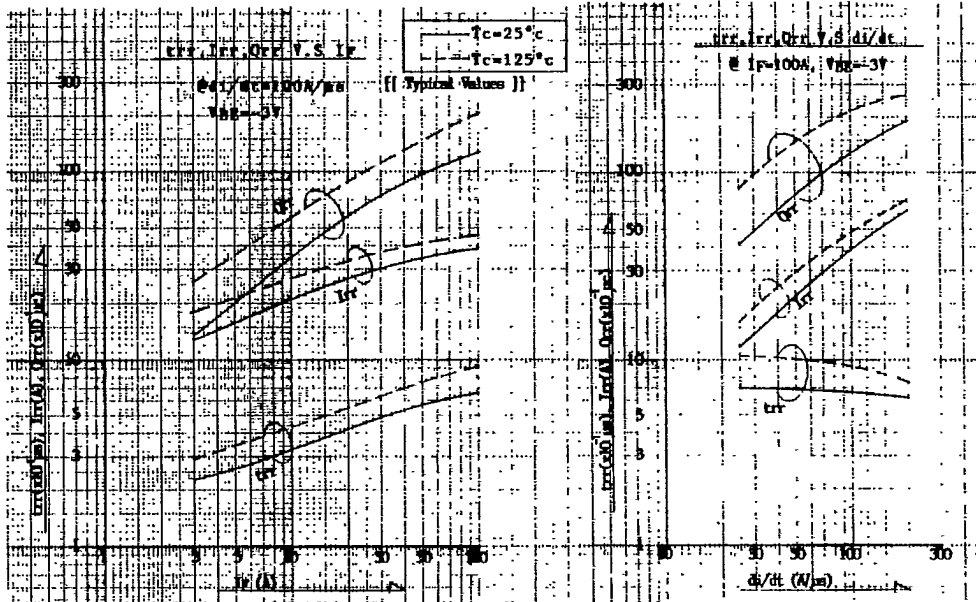
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SEMICONDUCTOR  
TECHNICAL DATA

MG100G1JL1  
MG100G2CL1  
MG100G2DL1



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